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Sheet 1 of 1

Complete if Known

Application Number	10/650,445
Filing Date	8/28/2003
First Named Inventor	Lin, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM02-1369

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
ON	1	US-4,998,510	03-12-1991	Rognon	
ON	2	US-8,137,149	10-24-2000	Kodama	
ON	3	US-8,420,218 B1	07-16-2002	Yu	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ^o
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
ON	4	Chau, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM, pp. 621-624, 2001.	
ON	5	Choi, Y.K., et al., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era," IEEE Electron Device Letters, Vol. 21, No. 5, pp. 254-255, May 2000.	
ON	6	Yeo, Y.C., et al., "Design and Fabrication of 50-nm Thin-Body p-MOSFETs with a SiGe Heterostructure Channel," IEEE Transactions on Electron Devices, Vol. 49, No. 2, pp. 279-286, February 2002.	

Examiner Signature	ON	Date Considered	7/14/05
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